L Number	Hits	Search Text	DB	Time stamp
9	0	438/525.197.ccls. and (field adj effect	USPAT;	2003/11/17
"	· ·	adj transistor) and (ion adj implant) and	US-PGPUB;	08:33
		day transistory and tron ady imprant, and	EPO; JPO;	00.33
		(angl\$3 with dopant)	· ·	
		161 2 2 11 66 1 21 to 10 11 to 10 11 11 11 11 11 11 11 11 11 11 11 11	DERWENT	2002/11/02
-	2124	(field adj effect adj transistor) and	USPAT;	2003/11/03
		(ion adj implant)	US-PGPUB;	16:16
			EPO; JPO;	
			DERWENT	
l <u>-</u>	6	438/525.ccls. and (field adj effect adj	USPAT;	2003/11/17
		transistor) and (ion adj implant) and	US-PGPUB;	08:32
		(angl\$3 with dopant)	EPO; JPO;	
		(angres wrom aspane)	DERWENT	
	85	(field adj effect adj transistor) and	USPAT;	2003/06/20
_	05	(ion adj implant) and (angl\$3 with	US-PGPUB;	19:01
				1 19.01
		dopant)	EPO; JPO;	
			DERWENT	
-	34	(field adj effect adj transistor) and	USPAT;	2003/06/20
		(ion adj implant) and (angl\$3 with	US-PGPUB;	18:56
		dopant) and (gate adj electrode)	EPO; JPO;	
			DERWENT	
_	34	(field adj effect adj transistor) and	USPAT;	2003/06/21
-	34	(ion adj implant) and (angl\$3 with	US-PGPUB;	13:44
		(10n adj 1mp1ant) and (angl\$3 with   dopant) and (gate adj electrode) and	EPO; JPO;	
		dopant) and (gate adj electrode) and	DERWENT	
	1	(source) and (drain)		2003/06/20
<u>-</u>	5	(field adj effect adj transistor) and	USPAT;	
		(ion adj implant) and (angl\$3 with	US-PGPUB;	18:59
	ļ	dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (lithography)	DERWENT	
_	l o	(field adj effect adj transistor) and	USPAT;	2003/10/30
		(ion adj implant) and (angl\$3 with	US-PGPUB;	08:59
	ļ	dopant) and (gate adj electrode) and	EPO; JPO;	1
	}	(source) and (drain) and (pocket adj	DERWENT	1
İ				
		region)   438/197.ccls. and (field adj effect adj	USPAT;	2003/06/20
-	4	438/19/.ccis. and (field ad) effect adj	US-PGPUB;	19:02
		transistor) and (ion adj implant) and		19.02
1		(angl\$3 with dopant)	EPO; JPO;	
			DERWENT	1 / /
_	27		USPAT;	2003/06/20
		(ion adj implant) and (angl\$3 with	US-PGPUB;	19:04
		dopant) and (gate adj electrode) and	EPO; JPO;	
	1	(source) and (drain) and (mask)	DERWENT	
1_	0	1	USPAT;	2003/06/20
	1	(ion adj implant) and (angl\$3 with	US-PGPUB;	19:05
		dopant) and (gate adj electrode) and	EPO; JPO;	
İ		(source) and (drain) and (mask) and	DERWENT	
	ļ		2011111111	
		(conductive adj region)	HCDATT.	2003/06/20
-	5	(field adj effect adj transistor) and	USPAT;	1 = 1 1
		(ion adj implant) and (angl\$3 with	US-PGPUB;	19:05
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (mask) and	DERWENT	
		(conductive adj layer)		
-	6	(field adj effect adj transistor) and	USPAT;	2003/06/20
	1	(ion adj implant) and (angl\$3 with	US-PGPUB;	19:06
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (mask) and	DERWENT	
		(conduct\$3 adj layer)	USPAT;	2003/06/21
-	18		1	15:51
		(ion adj implant) and (angl\$3 with	US-PGPUB;	12:21
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (mask with	DERWENT	1
1		electrode)		
_	12		USPAT;	2003/06/21
		(ion adj implant) and (angl\$3 with	US-PGPUB;	16:05
		dopant) and (gate adj electrode) and	EPO; JPO;	1
	1	(source) and (drain) and (mask with	DERWENT	
1			PRIVATIAT	
ı	1	spacer)	_l	

-	1	(field adj effect adj transistor) and	USPAT;	2003/06/21
		(ion adj implant) and (angl\$3 with	US-PGPUB;	15:57
1		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (mask with	DERWENT	
		dielectric adj spacer)		1
_	l ol		USPAT;	2003/06/21
		(ion adj implant) and (angl\$3 with	US-PGPUB;	16:07
		dopant) and (gate adj electrode) and	EPO; JPO;	
1	1	(source) and (drain) and (taper with	DERWENT	
1			DUKWUU.	
	ا ا	electrode)	USPAT;	2003/06/21
-	0	(field adj effect adj transistor) and	·	16:11
		(ion adj implant) and (angl\$3 with	US-PGPUB;	10:11
		dopant) and (gate adj electrode) and	EPO; JPO;	
		(source) and (drain) and (taper\$2 with	DERWENT	
		electrode)		0000/05/04
-	5		USPAT;	2003/06/21
		(ion adj implant) and (angl\$3 with	US-PGPUB;	16:12
		dopant) and (gate adj electrode) and	EPO; JPO;	
1		(source) and (drain) and (reduced with	DERWENT	1
		electrode)		
1_	0	I	USPAT;	2003/06/27
-	"	1203027 · 17·414·	US-PGPUB;	08:41
			EPO; JPO;	
			DERWENT	
		ED 1262027 6 did	USPAT;	2003/06/27
-	2	EP-1263027-\$.did.	US-PGPUB;	09:04
				05.03
			EPO; JPO;	
			DERWENT	2003/06/27
-	12213048	US 5731239.pn.	USPAT;	2003/06/27
			US-PGPUB;	08:54
			EPO; JPO;	
			DERWENT	į į
_	2	5731239.pn.	USPAT;	2003/06/27
	_	0,0220,0	US-PGPUB;	08:57
			EPO; JPO;	
			DERWENT	!
		512063.pn.	USPAT;	2003/06/27
-	4	512063.pm.	US-PGPUB;	08:58
			EPO; JPO;	
	1		DERWENT	
	_		USPAT;	2003/06/27
-	2	5120637.pn.	US-PGPUB;	08:58
100			1	00.50
			EPO; JPO;	
			DERWENT	0000 (06 (07
-	2	5120673.pn.	USPAT;	2003/06/27
			US-PGPUB;	09:10
			EPO; JPO;	
			DERWENT	1 1
_	0	JP-88317951-\$.did.	USPAT;	2003/06/27
1	1	·	US-PGPUB;	09:23
			EPO; JPO;	1
			DERWENT	
1_	1 0	JP-2162738-\$.did.	USPAT;	2003/06/27
1	1	01 1101.00 7.010.	US-PGPUB;	09:06
1			EPO; JPO;	
1			DERWENT	
1		TD 01(0739 7 6 444	USPAT;	2003/06/27
-	0	JP-2162738 A-\$.did.	US-PGPUB;	09:07
1				03.07
			EPO; JPO;	
1			DERWENT	2002/06/27
-	2	5021355.pn.	USPAT;	2003/06/27
1			US-PGPUB;	09:13
1			EPO; JPO;	
			DERWENT	
1_	2	6501133.pn.	USPAT;	2003/06/27
	"		US-PGPUB;	09:15
1	1		EPO; JPO;	
	1		DERWENT	1
	0	2020050621 pp	USPAT;	2003/06/27
_	I "	2020050621.pn.	US-PGPUB;	09:25
	1			*5.25
	1		EPO; JPO;	1
i	1		DERWENT	1

-	0	2000648044.pn.	USPAT;	2003/06/27
			US-PGPUB;	09:17
			EPO; JPO;	
			DERWENT	2002/06/07
-	2	20020050621.pn.	USPAT;	2003/06/27
			US-PGPUB;	09:18
			EPO; JPO;	
İ			DERWENT	2002/06/27
-	2	5731239.pn.	USPAT;	2003/06/27
			US-PGPUB;	09:19
			EPO; JPO; DERWENT	
		5100673	USPAT;	2003/06/27
-	2	5120673.pn.	US-PGPUB;	09:19
			EPO; JPO;	09.19
			DERWENT	
1	1	JP-56048174-\$.did.	USPAT;	2003/06/27
-	1	0F-30040174-\$.did.	US-PGPUB;	09:23
			EPO; JPO;	
1			DERWENT	[
_	2	5021355.pn.	USPAT;	2003/06/27
-		3021333.p	US-PGPUB;	09:25
1			EPO; JPO;	
			DERWENT	
_	10	438/525,197.ccls. and (field adj effect	USPAT;	2003/06/27
		adj transistor) and (ion adj implant) and	US-PGPUB;	10:11
		(angl\$3 with dopant)	EPO; JPO;	
			DERWENT	
-	221	mask with (dielectric adj spacer)	USPAT;	2003/10/30
			US-PGPUB;	09:02
			EPO; JPO;	
			DERWENT	
1 -	14806	(advanced adj micro adj devices).asn.	USPAT;	2003/11/03
			US-PGPUB;	16:19
İ			EPO; JPO;	
1			DERWENT	0003 (11 (03
-	42		USPAT;	2003/11/03
		mask and shadow	US-PGPUB;	16:19
			EPO; JPO;	
			DERWENT	2003/11/03
-	10	(advanced adj micro adj devices).asn. and	USPAT; US-PGPUB;	16:20
		mask and shadow and gate adj electrode	EPO; JPO;	10.20
•			DERWENT	
1		438/519.ccls. and (advanced adj micro adj	USPAT;	2003/11/03
-	0	devices).asn. and mask and shadow and	US-PGPUB;	16:21
		gate adj electrode	EPO; JPO;	]
1		gate auj effectione	DERWENT	
1_	10	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
-		and mask and shadow and gate adj	US-PGPUB;	10:17
		electrode	EPO; JPO;	
1			DERWENT	
-	0	(advanced adj micro adj devices).asn.	USPAT;	2003/11/03
		and (reduced adj width adj mask) and	US-PGPUB;	16:26
1	[	shadow and gate adj electrode	EPO; JPO;	
			DERWENT	
-	0		USPAT;	2003/11/03
		and (mask same (reduced adj width)) and	US-PGPUB;	16:28
1		shadow and gate adj electrode	EPO; JPO;	
			DERWENT	2002/11/04
-	0		USPAT;	2003/11/04
		and (mask same reduced same width) and	US-PGPUB;	09:14
		shadow and gate adj electrode	EPO; JPO;	
	_		DERWENT	2003/11/04
-	2		USPAT; US-PGPUB;	09:50
		and (mask same width) and shadow and gate	EPO; JPO;	33.30
		adj electrode	DERWENT	
	2	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
-	4	and (mask same width) and shadow and gate	US-PGPUB;	09:54
		and (mask same width) and shadow and gate adj electrode and mask	EPO; JPO;	
		au crootrous and mass	DERWENT	

_	2	4198250.pn.	USPAT;	2003/11/04
			US-PGPUB;	09:55
			EPO; JPO;	
			DERWENT	
_	6	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
	_	and mask and shadow and gate adj	US-PGPUB;	10:38
		electrode and width	EPO; JPO;	
			DERWENT	
l <b>–</b>	212	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
		and mask and (gate same width same mask)	US-PGPUB;	10:39
		.,,	EPO; JPO;	
			DERWENT	
_	212	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
		and (gate same width same mask)	US-PGPUB;	10:48
			EPO; JPO;	
			DERWENT	
_	1	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
		and (gate same width same mask same	US-PGPUB;	10:49
		implementation)	EPO; JPO;	
		•	DERWENT	
_	27	(advanced adj micro adj devices).asn.	USPAT;	2003/11/04
		and (implanting same width same mask)	US-PGPUB;	10:49
			EPO; JPO;	
			DERWENT	
_	51		USPAT;	2003/11/04
		and (gate same width same mask same	US-PGPUB;	10:49
		implantation)	EPO; JPO;	
1			DERWENT	